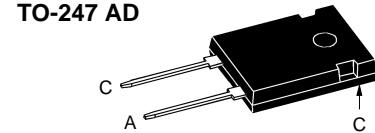
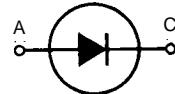


Fast Recovery Epitaxial Diode (FRED)

DSEI 30

I_{FAVM} = 26 A
V_{RRM} = 1200 V
t_{rr} = 40 ns

V _{RSM}	V _{RRM}	Type
V	V	
1200	1200	DSEI 30-12A



A = Anode, C = Cathode

Symbol	Test Conditions	Maximum Ratings	
I _{FRMS}	T _{VJ} = T _{VJM}	70	A
I _{FAVM} ①	T _C = 85°C; rectangular, d = 0.5	26	A
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	375	A
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	200	A
	t = 8.3 ms (60 Hz), sine	210	A
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	185	A
	t = 8.3 ms (60 Hz), sine	195	A
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	200	A ² s
	t = 8.3 ms (60 Hz), sine	180	A ² s
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	170	A ² s
	t = 8.3 ms (60 Hz), sine	160	A ² s
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	138	W
M _d	Mounting torque	0.8...1.2	Nm
Weight		6	g

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
I _R	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 25°C V _R = 0.8 • V _{RRM} T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	750 250 7	µA µA mA
V _F	I _F = 30 A; T _{VJ} = 150°C T _{VJ} = 25°C	2.2 2.55	V V
V _{To}	For power-loss calculations only	1.65	V
r _T	T _{VJ} = T _{VJM}	18.2	mΩ
R _{thJC}		0.9	K/W
R _{thCK}		35	K/W
R _{thJA}		0.25	K/W
t _{rr}	I _F = 1 A; -di/dt = 100 A/µs; V _R = 30 V; T _{VJ} = 25°C	40	60 ns
I _{RM}	V _R = 540 V; I _F = 30 A; -di _F /dt = 240 A/µs L ≤ 0.05 µH; T _{VJ} = 100°C	16	18 A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}, V_R = 0.8 V_{RRM}, duty cycle d = 0.5

Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions